



## TO-92MOD Plastic-Encapsulate Transistors

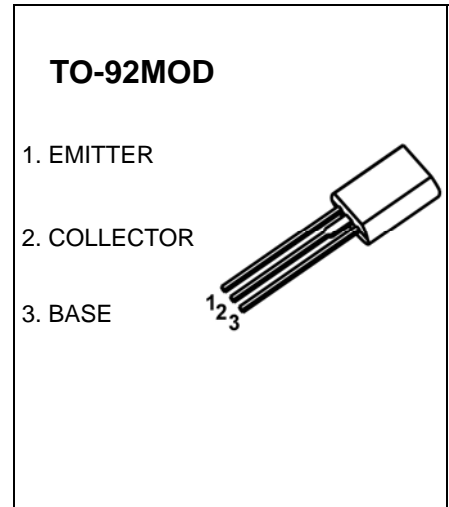
### 2SA966 TRANSISTOR (PNP)

#### FEATURE

- Complementary to 2SC2236 and 3 Watts output Applications.

#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted )

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-1.5	A
P <sub>c</sub>	Collector Power Dissipation	0.9	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> = -1mA, I <sub>E</sub> =0	-30			V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> = -500mA	100		320	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -1.5 A, I <sub>B</sub> = -0.03A			-2	V
Base-emitter voltage	V <sub>BE</sub>	I <sub>C</sub> = -500mA, V <sub>CE</sub> =-2V			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> =-500mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz			30	pF

#### CLASSIFICATION OF h<sub>FE</sub>

Rank	O	Y
Range	100-200	160-320